

/ Descriptions

PDFN3×3A-8L N MOS

N-Channel Enhancement Mode Field Effect Transistor in a PDFN3×3A-8L Plastic Package.

/ Features

$V_{DS} (V) = 30V$ $I_D = 66A$ ($V_{GS} = \pm 20V$)

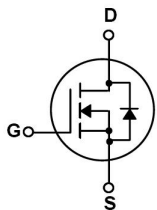
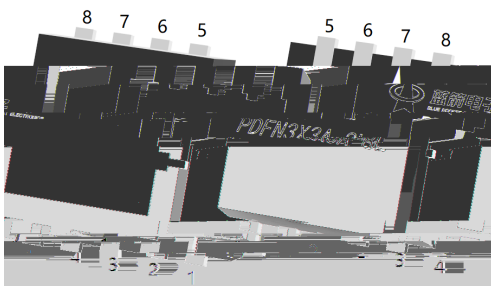
$R_{DS(ON)}@10V \leq 4.2m\Omega$ (Typ.4.0m Ω)

$R_{DS(ON)}@4.5V \leq 8.0m\Omega$ (Typ.5.3m Ω)

HF Product.

/ /1T05.p

Load Switch Applications,Battery Power Management.



/ Marking

See Marking Instructions.

BRCS040N03YB

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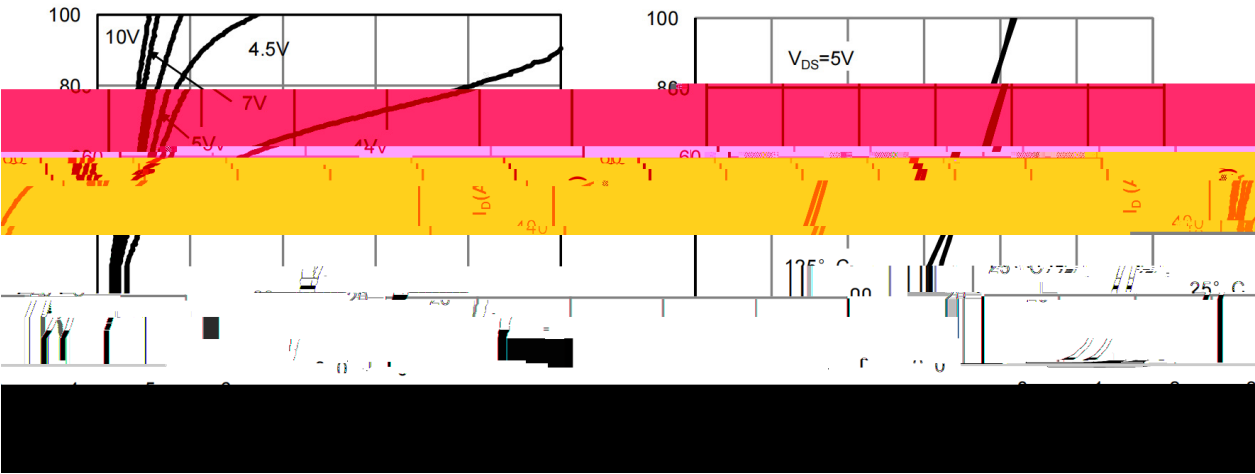
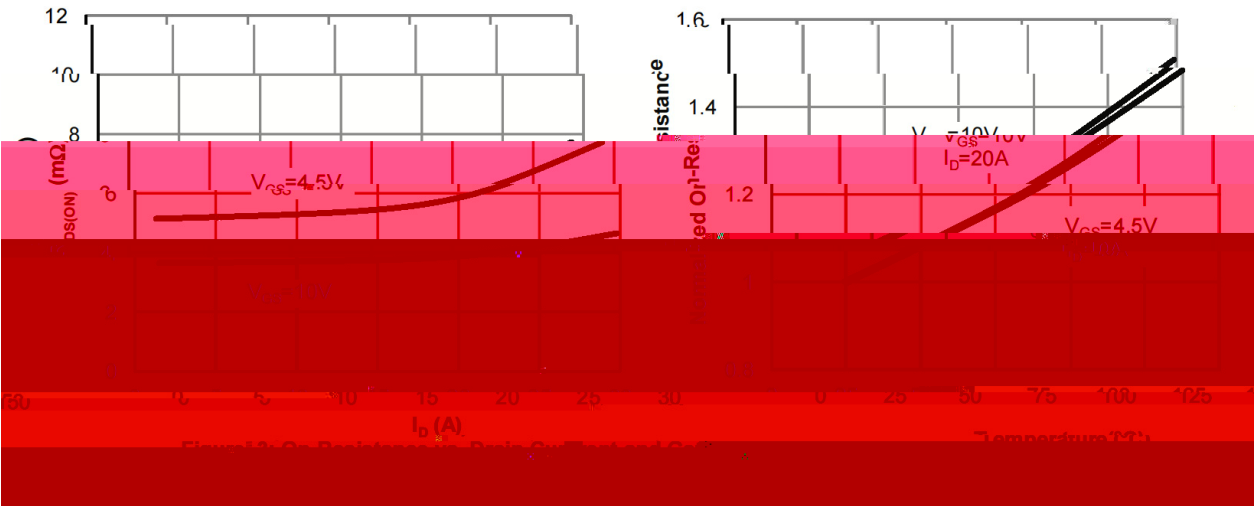
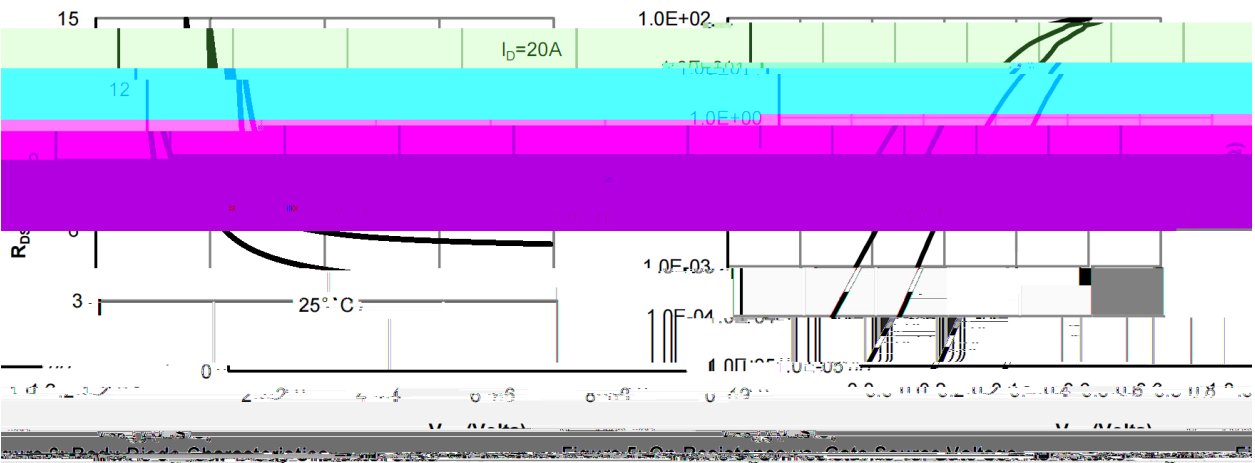
DATA SHEET

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	30	V
Drain Current		$I_D(T_c=25^\circ\text{C})$	66	A
Peak Drain Current		I_{DM}	170	A
Gate-Source Voltage		V_{GS}	± 20	V
Avalanche Current		I_{AS}	24.3	A
Single Pulsed Avalanche Energy		E_{AS}	295	mJ
Total Power Dissipation		$P_D(T_c=25^\circ\text{C})$	33	W
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	
Thermal resistance, junction - ambient	$t \leq 10\text{s}$	$R_{\theta JA}$	40	/W
	Steady-State		75	
Thermal resistance, junction - case	Steady-State	$R_{\theta JC}$	3.8	

Parameter Symbol Test Conditions @f

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Total Gate Charge	$Q_{g(10V)}$	$V_{GS}=10V,$ $I_D=20A$ $V_{DS}=15V,$	U			

/ Electrical Characteristic Curve



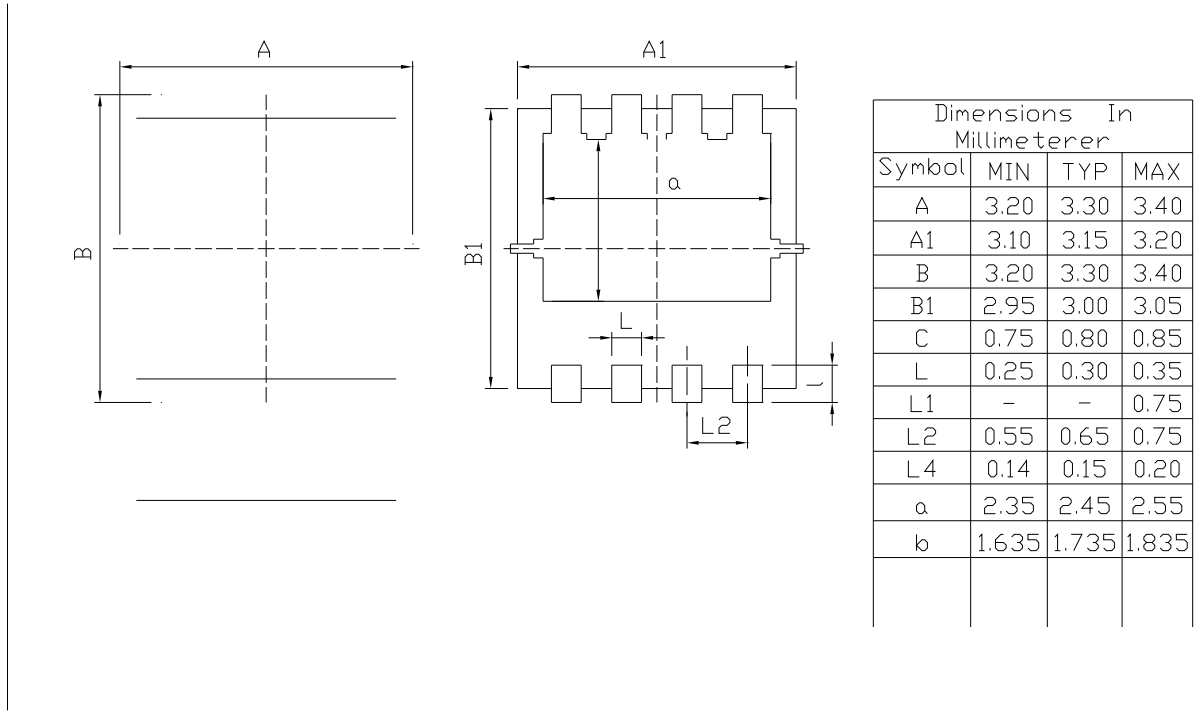
/ Electrical Characteristic Curve



/ Package Dimensions

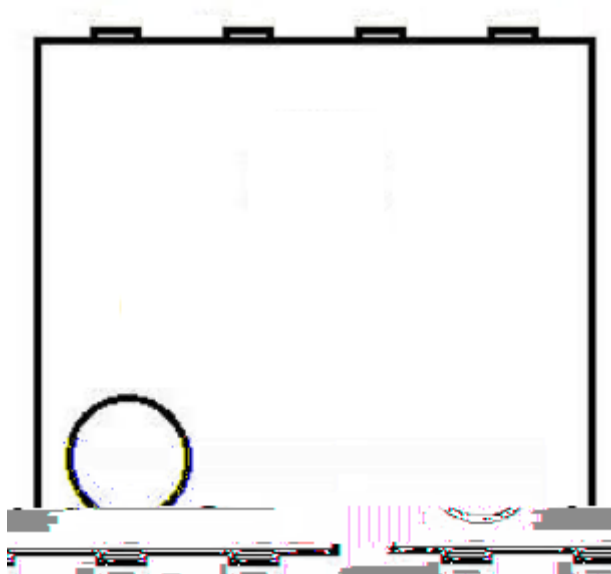
PDFN3X3A-8L

Unit:mm



Rev.00 202011

/ Marking Instructions



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040N03

Note:

BR: Company Code

040N03: Product Type Code

****: Lot No. Code, code change with Lot No

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DATA SHEET